
nless otherwise specified)

	V_{DRM} /$_{RRM}$	1800	V
	V_{DSM} /$_{RSM}$	1900	V
	$I_{D(AV)}$	75	A
	I_{TSM}	900	A
	I^2t	4050	A2s
	di/dt	150	A/µs
	dv/dt	1000	V/µs

(@ T_C = 25℃ unless otherwise specified)

Forward voltage	I_T=75A	V_{TM}		1.10	1.30	V
Repetitive peak off-state current	V_D = V_{DRM}, T_{vj} = 25℃	I_{DRM}			0.1	mA
	V_D = V_{DRM}, T_{vj} = 125℃				20	mA
Reverse leakage current	V_R = V_{RRM}, T_{vj} = 25℃	I_{RRM}			0.1	mA
	V_R = V_{RRM}, T_{vj} = 125℃				20	mA
Threshold voltage	For power loss calculation only T_{vj} = 125℃,	V_{TO}			0.85	V
Dynamic resistance	T_{vj} = 125℃,	r_T			2.5	mΩ
Triggering gate voltage	V_D=12V, R_L=30Ω	V_{GT}			1.8	V
Triggering gate current	V_D=12V, R_L=30Ω	I_{GT}	20		120	mA
Holding current	I_T=1A	I_H			250	mA

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(@ T_C = 25℃ unless otherwise specified)

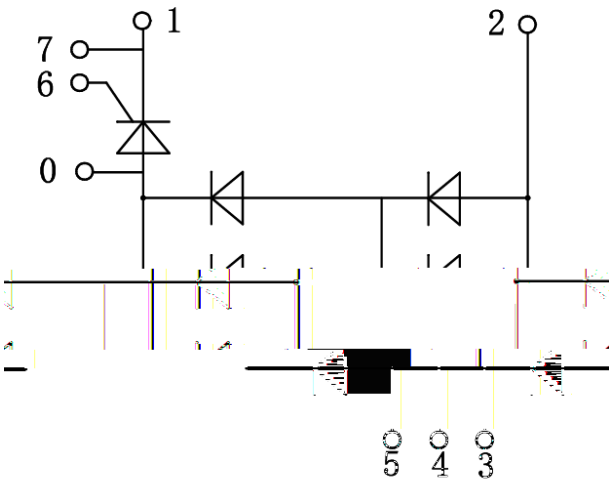
Forward voltage	I_D = 100A, Tvj = 25℃	V_F		1.20	1.40	V
Reverse leakage current	$V_R = V_{RRM}$, Tvj = 25℃	I_{RRM}			0.1	mA
	$V_R = V_{RRM}$, Tvj = 150℃				20	mA
Thermal resistance, junction to case	per diode	R_{thJC}			0.20	K/W

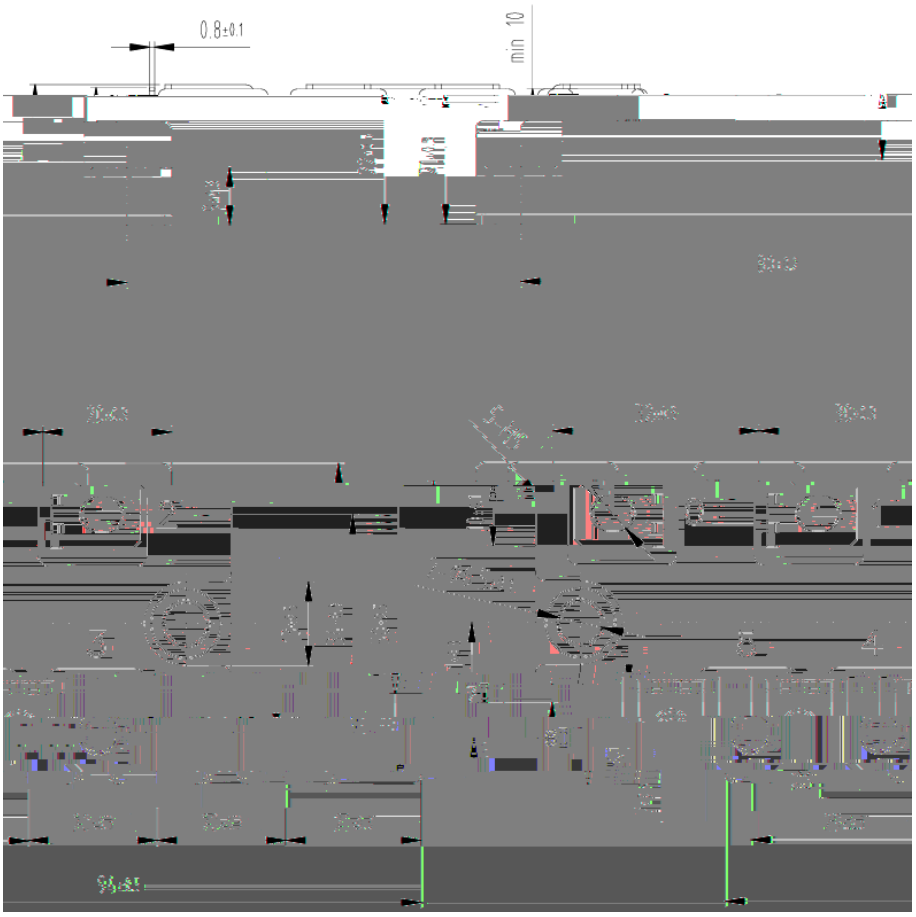
(@ T_C = 25℃ unless otherwise specified)

RMS isolation voltage	A.C 50Hz, 1min	V_{ISO}	3000			V
Thermal resistance, case to heatsink	per module	R_{thCS}			0.10	K/W
Maximum Junction Temperature	Thyristor	$T_{vj\ max}$			125	℃
	Diode				150	℃
Storage temperature range		T_{stg}	-40		125	℃
Mounting torque	To terminals(M5)	Mt	2.55		3.45	N·m
	To heatsinks(M5)	Ms	2.55		3.45	N·m

JMT75DS18L1	JMT75DS18L1	L1	210g/PCS	12 PCS	60 PCS

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Unit of measurement: mm

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